

# NSBC115TPDP6

## Complementary Bias Resistor Transistors R1 = 100 kΩ, R2 = ∞ kΩ

### NPN and PNP Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

#### Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS

(T<sub>A</sub> = 25°C both polarities Q1 (PNP) and Q2 (NPN), unless otherwise noted)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V <sub>CB0</sub>	50	Vdc
Collector-Emitter Voltage	V <sub>CEO</sub>	50	Vdc
Collector Current - Continuous	I <sub>C</sub>	100	mAdc
Input Forward Voltage	V <sub>IN(fwd)</sub>	40	Vdc
Input Reverse Voltage	V <sub>IN(rev)</sub>		Vdc
-NPN		6	
-PNP		5	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NSBC115TPDP6T5G	SOT-963	8,000 / Tape & Reel

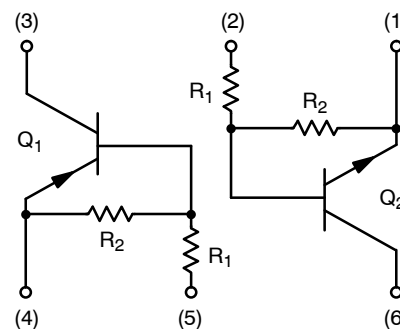
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



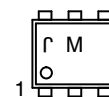
ON Semiconductor®

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#### PIN CONNECTIONS



#### MARKING DIAGRAMS



SOT-963  
CASE 527AD

J = Specific Device Code  
M = Date Code\*

\*Date Code orientation may vary depending upon manufacturing location.

# NSBC115TPDP6

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
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### NSBC115TPDP6 (SOT-963) One Junction Heated

Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 1) (Note 2)	$P_D$	231	mW
Derate above $25^\circ\text{C}$ (Note 1) (Note 2)		1.9	$\text{mW}/^\circ\text{C}$
Thermal Resistance, Junction to Ambient (Note 1) (Note 2)	$R_{\theta JA}$	540	$^\circ\text{C}/\text{W}$
		464	

### NSBC115TPDP6 (SOT-963) Both Junction Heated (Note 3)

Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 1) (Note 2)	$P_D$	339	mW
Derate above $25^\circ\text{C}$ (Note 1) (Note 2)		2.7	$\text{mW}/^\circ\text{C}$
Thermal Resistance, Junction to Ambient (Note 1) (Note 2)	$R_{\theta JA}$	369	$^\circ\text{C}/\text{W}$
		306	
Junction and Storage Temperature Range	$T_J, T_{\text{stg}}$	-55 to +150	$^\circ\text{C}$

- FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
- FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.
- Both junction heated values assume total power is sum of two equally powered channels.

# NSBC115TPDP6

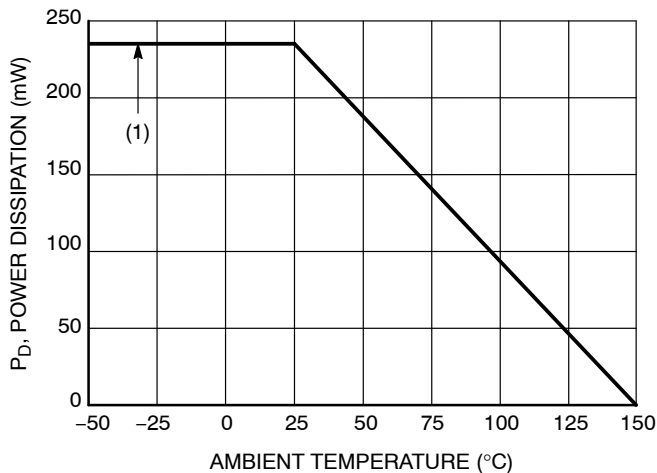
## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C both polarities Q<sub>1</sub> (PNP) and Q<sub>2</sub> (NPN), unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector-Base Cutoff Current (V <sub>CB</sub> = 50 V, I <sub>E</sub> = 0)	I <sub>CBO</sub>	-	-	100	nAdc
Collector-Emitter Cutoff Current (V <sub>CE</sub> = 50 V, I <sub>B</sub> = 0)	I <sub>CEO</sub>	-	-	500	nAdc
Emitter-Base Cutoff Current (V <sub>EB</sub> = 6.0 V, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	-	0.1	mAdc
Collector-Base Breakdown Voltage (I <sub>C</sub> = 10 μA, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (Note 4) (I <sub>C</sub> = 2.0 mA, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	50	-	-	Vdc

## ON CHARACTERISTICS

DC Current Gain (Note 4) (I <sub>C</sub> = 5.0 mA, V <sub>CE</sub> = 10 V)	h <sub>FE</sub>	160	350	-	
Collector-Emitter Saturation Voltage (Note 4) (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 1.0 mA)	V <sub>CE(sat)</sub>	-	-	0.25	Vdc
Input Voltage (off) (V <sub>CE</sub> = 5.0 V, I <sub>C</sub> = 100 μA) (NPN) (V <sub>CE</sub> = 5.0 V, I <sub>C</sub> = 100 μA) (PNP)	V <sub>i(off)</sub>	-	0.6 0.62	-	Vdc
Input Voltage (on) (V <sub>CE</sub> = 0.2 V, I <sub>C</sub> = 1.0 mA) (NPN) (V <sub>CE</sub> = 0.2 V, I <sub>C</sub> = 1.0 mA) (PNP)	V <sub>i(on)</sub>	-	1.0 1.0	-	Vdc
Output Voltage (on) (V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 3.5 V, R <sub>L</sub> = 1.0 kΩ)	V <sub>OL</sub>	-	-	0.2	Vdc
Output Voltage (off) (V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 0.25 V, R <sub>L</sub> = 1.0 kΩ)	V <sub>OH</sub>	4.9	-	-	Vdc
Input Resistor	R <sub>1</sub>	70	100	130	kΩ
Resistor Ratio	R <sub>1</sub> /R <sub>2</sub>	-	-	-	

4. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.



(1) SOT-963; 100 mm<sup>2</sup>, 1 oz. copper trace

Figure 1. Derating Curve

# NSBC115TPDP6

## TYPICAL CHARACTERISTICS – NPN TRANSISTOR NSBC115TPDP6

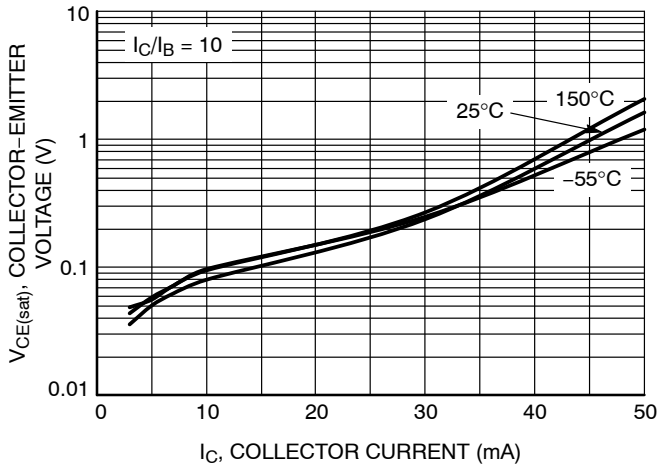


Figure 2.  $V_{CE(sat)}$  vs.  $I_C$

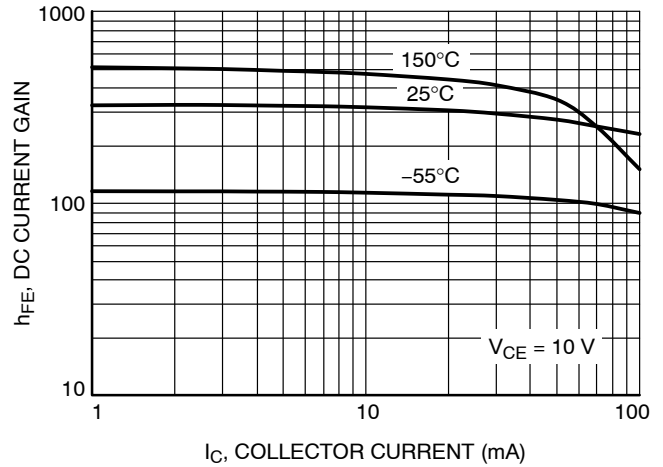


Figure 3. DC Current Gain

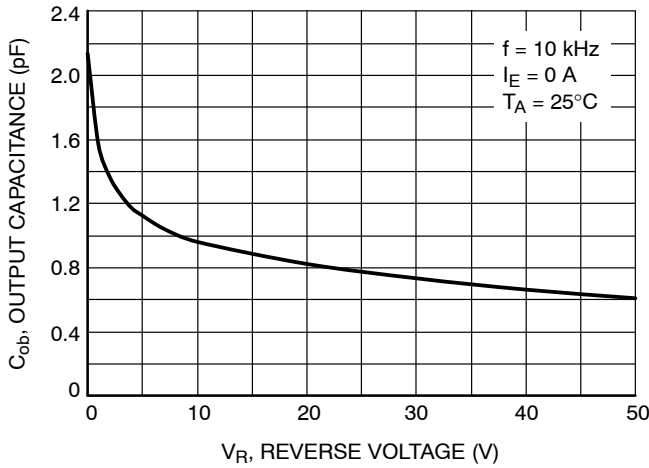


Figure 4. Output Capacitance

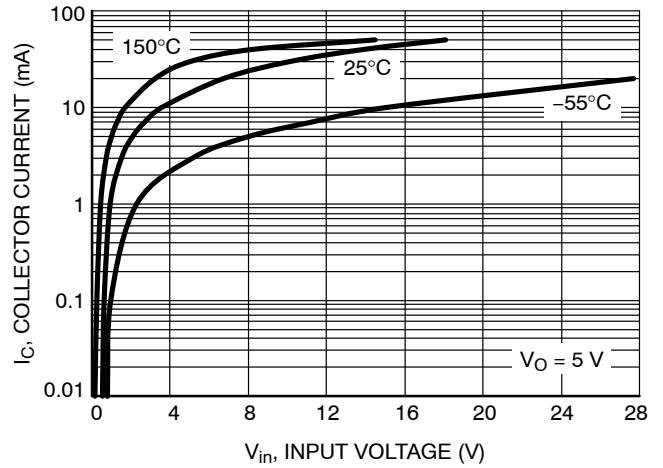


Figure 5. Output Current vs. Input Voltage

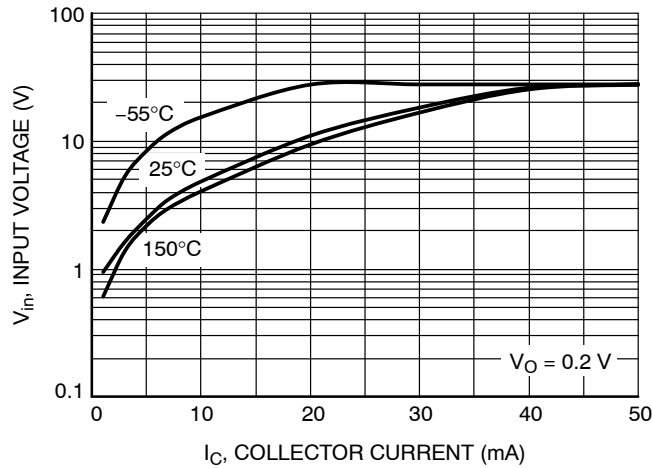


Figure 6. Input Voltage vs. Output Current

# NSBC115TPDP6

## TYPICAL CHARACTERISTICS – PNP TRANSISTOR NSBC115TPDP6

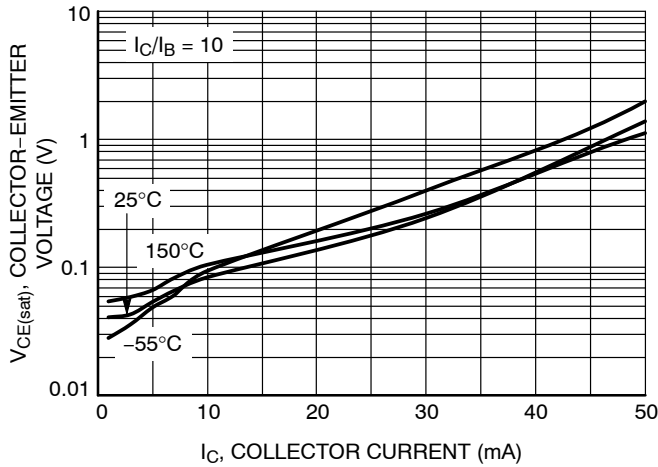


Figure 7.  $V_{CE(sat)}$  vs.  $I_C$

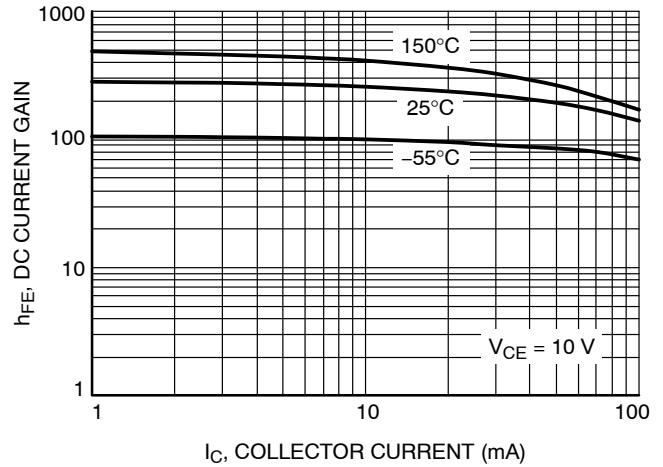


Figure 8. DC Current Gain

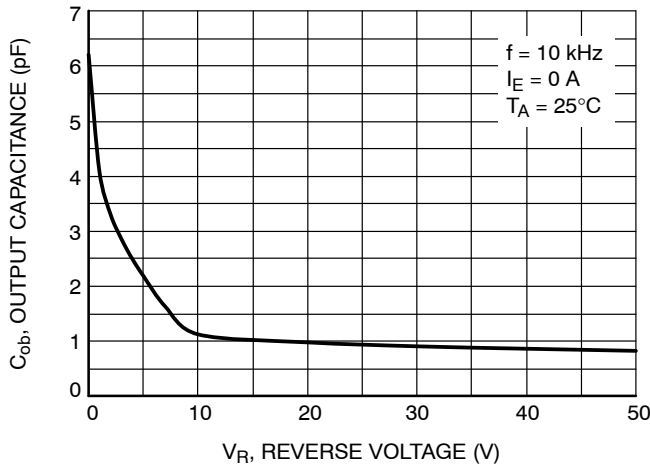


Figure 9. Output Capacitance

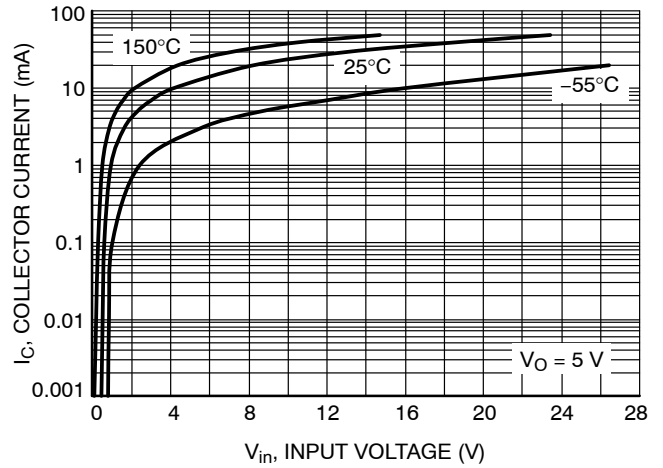


Figure 10. Output Current vs. Input Voltage

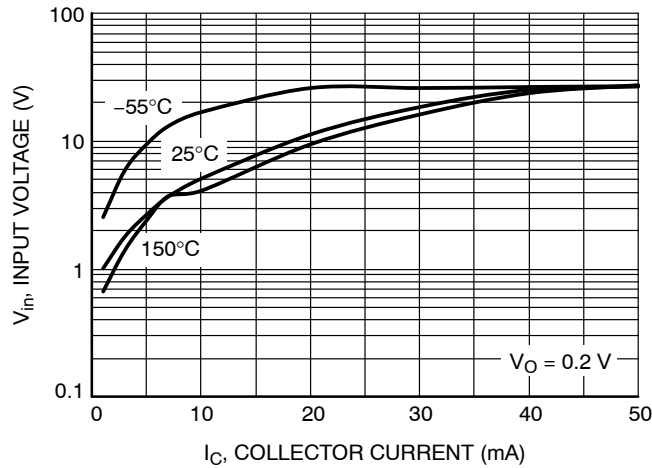
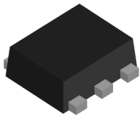


Figure 11. Input Voltage vs. Output Current

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

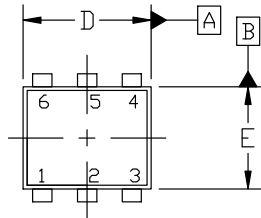


**SOT-963 1.00x1.00x0.37, 0.35P**  
**CASE 527AD**  
**ISSUE F**

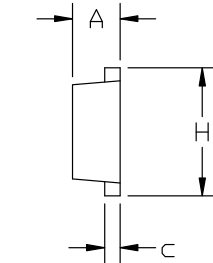
DATE 20 FEB 2024

**NOTES:**

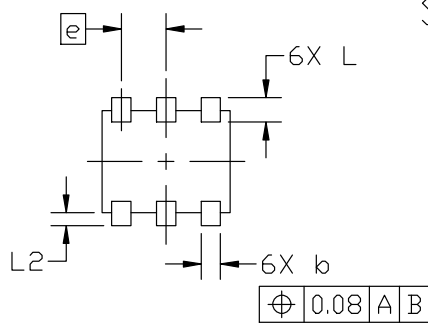
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.



TOP VIEW

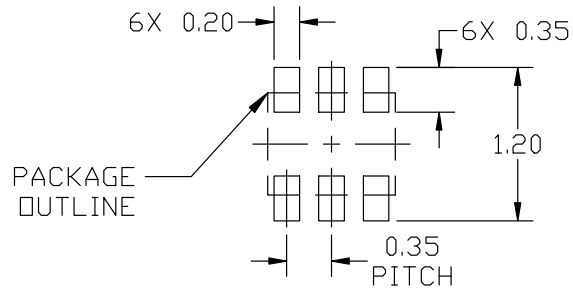


SIDE VIEW



BOTTOM VIEW

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.34	0.37	0.40
b	0.10	0.15	0.20
c	0.07	0.12	0.17
D	0.95	1.00	1.05
E	0.75	0.80	0.85
e	0.35 BSC		
H	0.95	1.00	1.05
L	0.19 REF		
L2	0.05	0.10	0.15

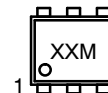


RECOMMENDED MOUNTING FOOTPRINT

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERRM/D.

- |  |   |  |
|--|---|--|
| <p><b>STYLE 1:</b><br/>         PIN 1. EMITTER 1<br/>         2. BASE 1<br/>         3. COLLECTOR 2<br/>         4. EMITTER 2<br/>         5. BASE 2<br/>         6. COLLECTOR 1</p> | <p><b>STYLE 2:</b><br/>         PIN 1. EMITTER 1<br/>         2. EMITTER2<br/>         3. BASE 2<br/>         4. COLLECTOR 2<br/>         5. BASE 1<br/>         6. COLLECTOR 1</p> | <p><b>STYLE 3:</b><br/>         PIN 1. CATHODE 1<br/>         2. CATHODE 1<br/>         3. ANODE/ANODE 2<br/>         4. CATHODE 2<br/>         5. CATHODE 2<br/>         6. ANODE/ANODE 1</p> |
| <p><b>STYLE 4:</b><br/>         PIN 1. COLLECTOR<br/>         2. COLLECTOR<br/>         3. BASE<br/>         4. EMITTER<br/>         5. COLLECTOR<br/>         6. COLLECTOR</p>      | <p><b>STYLE 5:</b><br/>         PIN 1. CATHODE<br/>         2. CATHODE<br/>         3. ANODE<br/>         4. ANODE<br/>         5. CATHODE<br/>         6. CATHODE</p>              | <p><b>STYLE 6:</b><br/>         PIN 1. CATHODE<br/>         2. ANODE<br/>         3. CATHODE<br/>         4. CATHODE<br/>         5. CATHODE<br/>         6. CATHODE</p>                       |
| <p><b>STYLE 7:</b><br/>         PIN 1. CATHODE<br/>         2. ANODE<br/>         3. CATHODE<br/>         4. CATHODE<br/>         5. ANODE<br/>         6. CATHODE</p>               | <p><b>STYLE 8:</b><br/>         PIN 1. DRAIN<br/>         2. DRAIN<br/>         3. GATE<br/>         4. SOURCE<br/>         5. DRAIN<br/>         6. DRAIN</p>                      | <p><b>STYLE 9:</b><br/>         PIN 1. SOURCE 1<br/>         2. GATE 1<br/>         3. DRAIN 2<br/>         4. SOURCE 2<br/>         5. GATE 2<br/>         6. DRAIN 1</p>                     |
| <p><b>STYLE 10:</b><br/>         PIN 1. CATHODE 1<br/>         2. N/C<br/>         3. CATHODE 2<br/>         4. ANODE 2<br/>         5. N/C<br/>         6. ANODE 1</p>              |   |  |

**GENERIC MARKING DIAGRAM\***



XX = Specific Device Code  
 M = Month Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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<b>DESCRIPTION:</b>	<b>SOT-963 1.00x1.00x0.37, 0.35P</b>	<b>PAGE 1 OF 1</b>

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